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U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

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Examiner Signature	<i>[Signature]</i>	Date Considered	<i>Apr 30, 2004</i>
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¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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filed 4-15-02

Form PTO-1449
(Rev. 8-83)

FEB 02 2004

U.S. Department of Commerce
Patent and Trademark Office

Atty Docket 0756-2415

Serial No. 10/026,802

INFORMATION DISCLOSURE STATEMENT

Applicants: Hisashi OHTANI et al.

Filing Date: December 27, 2001

Group Art Unit: 2812

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
<i>mu</i>	4,379,020	04/05/1983	Glaeser et al.			
<i>J</i>	5,614,426	03/25/1997	Funada et al.			
<i>J</i>	5,696,388	12/09/1997	Funada et al.			

FOREIGN PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
<i>mu</i>	01-276616	11/07/1989	JP			Eng Abst	
<i>J</i>	02-222546	09/05/1990	JP			Full Eng	
<i>J</i>	02-260524	10/23/1990	JP			Eng Abst	
<i>J</i>	07-058338	03/03/1995	JP			Eng Abst	
<i>J</i>	63-142807	06/15/1988	JP			Full Eng	

Examiner

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04/12/2002

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Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Complete if Known

Application Number	10/026,802
Filing Date	December 27, 2001
First Named Inventor	Hisashi Ohtani et al.
Group Art Unit	2811
Examiner Name	W. Mintel
Attorney Docket Number	0756-2415

U.S. PATENT DOCUMENTS

Examiner Initials ¹	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
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		Office ³	Number ⁴	Kind Code ⁵ (if known)				
/	/	JP	01-206632	/	/	08/18/1989	/	AB
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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i> APR 23 2004		Complete if Known	
Sheet 1 of 1		Application Number	10/026,802
		Filing Date	December 27, 2001
		First Named Inventor	Hisashi Ohtani et al.
		Group Art Unit	2811
		Examiner Name	Junghwa M. Im
		Attorney Docket Number	0756-2415

TRADEMARK		U.S. PATENT DOCUMENTS				
Examiner Initials ¹	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
W		4,801,351		Awane et al.	01/31/1989	
W		6,084,247		Yamazaki et al.	07/04/2000	
/						

[illegible]

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Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
Am		European Search Report dated March 5, 2004	

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		Filing Date	December 27, 2001
		First Named Inventor	Hisashi Ohtani et al.
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Sheet 1 of 1	Attorney Docket Number	0756-2415	

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Mw		4,801,351		Awane et al.	01/31/1989	
gr		6,084,247		Yamazaki et al.	07/04/2000	

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		Office ³	Number ⁴	Kind Code ⁵ (if known)				
Mw		JP	02-143415			06/01/1990		Abst.

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
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Mw		European Search Report dated March 5, 2004	

Examiner Signature	Date Considered	Exp 30. 2004
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Form PTO-1449 (Rev. 8-83)	U.S. Department of Commerce Patent and Trademark Office	Docket No: 740756-2415	Serial No. Not Yet Assigned			
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)						
		Applicant: Hisashi OHTANI et al.				
		Filing Date: December 27, 2001	Group: 2811			
U.S. PATENT DOCUMENTS						
Examiner Initial	Document Number	Date	Name	Class	Subclasses	Filing Date (if appropriate)
	5,949,091	09/07/1999	Yamaguchi			
	5,488,000	01/30/1996	Zhang et al.			
	5,605,846	02/25/1997	Ohtani et al.			
	4,933,298	06/12/1990	Hasegawa			
	4,766,477	08/23/1988	Nakagawa et al.			
	4,379,090	04/05/1996	Glaeser et al.			
	4,623,912	11/18/1986	Chang et al.			
	5,130,264	07/14/1992	Troxell et al.			
	5,608,232	03/04/1997	Yamazaki et al.			
	5,639,698	06/17/1997	Yamazaki et al.			
	5,882,960	03/16/1999	Zhang et al.			
	5,895,933	04/20/1999	Zhang et al.			
	5,897,347	04/27/1999	Yamazaki et al.			
	5,956,579	09/21/1999	Yamazaki et al.			
	FOREIGN PATENT DOCUMENTS					
	Document Number	Date	Country	Class	Subclass	Translation Yes No
	3-280420	12/11/1991	Japan			X
	0 390 608	10/03/1990	Japan			Abstract
	02-020059	01/23/1990	Japan			Abstract
	05-067635	03/19/1993	Japan			Abstract
	64-074754	03/20/1989	Japan			Abstract
	401135014	05/26/1989	Japan			Abstract
	WO 92/01089	01/23/1992	PCT			English
	EP 0 612 102 A3	08/24/1994	Europe			
	EP 0 631 325 A3	12/28/1994	Europe			
✓	WO 86/03621	06/19/1986	WIPO			
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)						
	Batstone et al., "Microscopic Processes in Crystallization", Solid State Phenomena, Vols. 37-38, pp. 257-268					
	Graef et al., "Enhanced Crystallinity of Silicon Films Deposited by CVD on Liquid Layers (CVDOLLProcess): Silicon on Tin Layers in the Presence of Hydrogen Chloride", Journal of Applied Physics, Vol. 48, No. 9, September 1977, pp. 3937-3940					
Examiner	Date Considered					
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U.S. PATENT DOCUMENTS						
Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
	5,352,291	10/04/1994	Zhang et al			
	4,309,224	01/05/1982	Shibata			
	5,278,093	01/11/1994	Yonehara			
	5,529,937	06/25/1996	Zhang et al			
	5,481,121	01/02/1996	Zhang et al			
	5,219,786	06/15/1993	Noguchi			
	5,605,846	02/25/1997	Ohtani et al			
	5,426,064	06/20/1995	Zhang et al			
	4,746,628	05/24/1988	Takafuji et al			
	5,130,103	07/14/1992	Yamagata et al			
	5,010,033	04/23/1991	Tokunaga et al			
	5,501,989	03/26/1996	Takayama et al			
	5,508,533	04/16/1996	Takemura			
	5,646,424	07/08/1997	Zhang et al			
	5,569,936	10/29/1996	Zhang et al			
	4,068,020	01/10/1978	Reuschel			
	3,108,914	10/29/1963	Hoerni			
	5,403,772	04/04/1995	Zhang et al			
	3,988,762	10/26/1976	Cline et al			
	3,783,049	01/01/1974	Sandera			
	5,608,232	03/04/1997	Yamazaki et al			
FOREIGN PATENT DOCUMENTS						
	Document Number	Date	Country	Class	Subclass	Translation Yes No
	60-105216	06/10/1985	Japan			Abstract
	4-11722 (Japanese & English)	01/16/1992	Japan			X
	2-140915 (Japanese & English)	05/30/1990	Japan			X
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)						
	Kakkad et al., "Crystallized Si Films by Low-Temperature Rapid Thermal Annealing of Amorphous Silicon", J. Appl. Phys., Vol. 65, No. 5, March 1, 1989, pp. 2069-2072					
	Kakkad et al., "Low Temperature Selective Crystallization of Amorphous Silicon", Journal of Non-Crystalline Solids 115 (1989), pp. 66-68					
	Liu et al., "Polycrystalline Silicon Thin Film Transistors on Corning 7059 Glass Substrates Using Short Time, Low-Temperature Processing", Appl. Phys. Lett., Vol. 62, No. 20, May 17, 1993, pp. 2554-2556					
	Liu et al., "Selective Area Crystallization of Amorphous Silicon Films by Low-Temperature Rapid Thermal Annealing", Appl. Phys. Lett., Vol. 55, No. 7, August 14, 1989, pp. 660-662					
Examiner		Date Considered				
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INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)							
				Applicant: Hisashi OHTANI et al.			
				Filing Date: December 27, 2001		Group: 2811	
U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
		5 1 4 7 8 2 6	09/15/1992	Liu et al.			
		5 3 8 7 5 3 0	02/07/1995	Doyle et al.			
		5 0 7 5 2 5 9	12/24/1991	Moran			
		5 2 4 4 8 3 6	09/14/1993	Lim			
		4 4 7 2 4 5 8	09/18/1984	Sirinyan et al.			
		5 3 5 8 9 0 7	10/25/1994	Wong			
		5 3 5 4 6 9 7	10/11/1994	Oostra et al.			
		4 9 1 1 7 8 1	03/27/1990	Fox et al.			
		3 3 8 9 0 2 4	06/18/1968	Schimmer			
	5 2 7 5 8 5 1	01/04/1994	Fonash et al.				
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
	C. Hayzelden et al., "In Situ Transmission Electron Microscopy Studies of Silicide-Mediated Crystallization of Amorphous Silicon", Appl. Phys. Lett. 62 (92) 225						
	S. P. Murarka, "Silicides for VLSI Applications", p. 112, 82						
	T. Hempel et al., Solid State Communications, Vol. 85, No. 11 (1993) pp. 921-924 "Needle-Like Crystallization of Ni Doped Amorphous Silicon Thin Films"						
	A. V. Dvurechenskii et al., Phys. Stat. Sol. (a) 95 (1986) pp. 635-640 "Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals"						
	J. Stoemenos et al., Appl. Phys. Lett., Vol. 58, No. 11, 18 March 1991, pp. 1196-1198 "Crystallization of Amorphous Silicon By Reconstructive Transformation Utilizing Gold"						
	C. Hayzelden et al., J. Appl. Phys., Vol. 73, No. 12, 15 June 1993, pp. 8279-8289, "Silicide Formation and Silicide-Mediated Crystallization of Nickel-Implanted Amorphous Silicon Thin Films"						
	A. Yu. Kuznetsov et al., Nucl. Instr. & Meth. Phys. Res. B80/81 (1993) pp. 990-993, "Enhanced Solid Phase Epitaxial Recrystallization of Amorphous Silicon Due to Nickel Silicide Precipitation Resulting From Ion Implantation and Annealing"						
	Y. Kawazu et al., Japanese Journal of Applied Physics, Vol. 29, No. 4, April 1990, pp. 729-738, "Initial Stage of the Interfacial Reaction between Nickel and Hydrogenated Amorphous Silicon"						
Examiner:				Date Considered: Apr 30, 2004			
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(Rev. 8-83)U.S. Department of Commerce
Patent and Trademark Office

Attorney Docket: 740756-2415

Serial No. Not Yet
Assigned**INFORMATION DISCLOSURE
STATEMENT**

(Use several sheets if necessary)

Applicant: Hisashi OHTANI, et al.

Filing Date: December 27, 2001

Group: 2811

U.S. PATENT DOCUMENTS

Examiner- Initial	Patent Number	Issue Date	Patentee	Class	Subclass	Filing Date (if approp.)
jm	4,933,298	06/12/1990	Hasegawa			
jm	5,923,962	07/13/1999	Ohtani et al.			
	5,643,826	07/01/1997	Ohtani et al.			
	5,531,182	07/02/1996	Yonehara			
	5,480,811	01/02/1996	Chiang et al.			
	5,492,843	02/20/1996	Adachi et al.			
	4,068,020	01/10/1978	Reuschel			
	4,959,247	09/25/1990	Moser et al.			
	5,492,843	02/20/1996	Adachi et al.			

I. FOREIGN PATENT DOCUMENTS

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jm	1-206632	11/15/1989	Japan			Abstract
jm	2-119122	05/07/1990	Japan			Abstract

OTHER DOCUMENTS (Including Author, Title, Relevant Pages, Date, Place of Publication)

jm	L. Hultman, et al., "CRYSTALLIZATION OF AMORPHOUS SILICON DURING THIN-FILM GOLD REACTION," J. Appl. Phys. 62(9), 1 November 1987, pp. 3647-3655.
	J.L. Batstone, et al., "MICROSCOPIC PROCESSES IN CRYSTALLISATION," [sic] Solid State Phenomena Vols. 37-38 (1994), pp. 257-268, 1994 Scitec Publications, Switzerland.
	S. Coffa, et al. (eds.), "CRUCIAL ISSUES IN SEMICONDUCTOR MATERIALS AND PROCESSING TECHNOLOGIES," pp. 483-499, 1992 Kluwer Academic Publishers.
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	M. Fuse, et al., "PERFORMANCE OF POLY-Si FILM TRANSISTORS FABRICATED BY EXCIMER-LASER ANNEALING OF SiH ₄ -and Si ₂ H ₆ - SOURCE LOW PRESSURE VAPOR DEPOSITED A Si FILMS WITH OR WITHOUT SOLID-PHASE CRYSTALLIZATION," Solid State Phenomena Vols. 37-38 (1994) pp. 565-570.
	S. Caune, et al., "COMBINED CW LASER AND FURNACE ANNEALING OF AMORPHOUS Si AND Ge IN CONTACT WITH SOME METALS," Applied Surface Science 36 (1989) pp. 597-604, North-Holland, Amsterdam.
	Oki et al., Short Notes, "Effect of Deposited Metals on the Crystallization Temperature of Amorphous Germanium Film", Japan J. Appl. Phys., 8 (1969) 1056, June 2, 1969, pp. 1056.

Examiner

Date Considered

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(use as many sheets as necessary)

Sheet	1	of	1	Attorney Docket Number	0756-2415
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Examiner Initials ²	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.

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Patent and Trademark Office

Atty Docket 0756-2415

Serial No. 10/026,802

INFORMATION DISCLOSURE STATEMENT

Applicants: Hisashi OHTANI et al.

Filing Date: December 27, 2001

Group Art Unit: 2812

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
<i>On</i>	4,379,020	04/05/1983	Glaeser et al.			
<i>On</i>	5,614,426	03/25/1997	Funada et al.			
<i>On</i>	5,696,388	12/09/1997	Funada et al.			

FOREIGN PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes No
<i>On</i>	01-276616	11/07/1989	JP			Eng Abst
<i>On</i>	02-222546	09/05/1990	JP			Full Eng
<i>On</i>	02-260524	10/23/1990	JP			Eng Abst
<i>On</i>	07-058338	03/03/1995	JP			Eng Abst
<i>On</i>	63-142807	06/15/1988	JP			Full Eng

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		Application Number	10/026,802
		Filing Date	December 27, 2001
		First Named Inventor	Hisashi Ohtani et al.
		Group Art Unit	2811
		Examiner Name	W. Mintel
Sheet 1 of 1	Attorney Docket Number	0756-2415	

U.S. PATENT DOCUMENTS						
Examiner Initials ¹	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ³ (if known)			

FOREIGN PATENT DOCUMENTS								
Examiner Initials ¹	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁴
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hm		JP	63-318162			12/27/1988		Abst.

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials ¹	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
hm		Ultra LSI Process Data Handbook, April 15, 1982, pp. 124-125	Concise Stmt.

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<i>[Signature]</i>	Apr 30 2002

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